

# **2019 19th Non-Volatile Memory Technology Symposium (NVMTS 2019)**

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# NVMTS2019

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*<sup>1</sup>Max Planck Institute for Microstructure Physics, <sup>2</sup>IBM Research, <sup>3</sup>Samsung Electronics, <sup>4</sup>Pohang University of Science and Technology, <sup>5</sup>Ecole Polytechnique Federale de Lausanne*

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*<sup>1</sup>ESL, Swiss Federal Institute of Technology Lausanne (EPFL), <sup>2</sup>University of Utah*

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<sup>1</sup>Fraunhofer IPMS-Center Nanoelectronic Technologies (CNT), <sup>2</sup>imec, <sup>3</sup>ESAT-KU Leuven